

CLAIMS

1. High purity hafnium and a target and thin film formed from said high purity hafnium having a purity of 4N or higher excluding zirconium and gas components,
5 and an oxygen content of 40wtppm or less.
2. High purity hafnium and a target and thin film formed from said high purity hafnium having a purity of 4N or higher excluding zirconium and gas components, and in which the content of sulfur and phosphorus is respectively 10wtppm or less.
3. High purity hafnium and a target and thin film formed from said high purity
10 hafnium according to claim 1 having a purity of 4N or higher excluding zirconium and gas components, and in which the content of sulfur and phosphorus is respectively 10wtppm or less.
4. High purity hafnium and a target and thin film formed from said high purity hafnium according to any one of claims 1 to 3 having a purity of 4N or higher
15 excluding zirconium and gas components, and in which the zirconium content is 0.5wt% or lower.
5. A manufacturing method of high purity hafnium wherein a hafnium sponge raw material is subject to solvent extraction and thereafter dissolved, and the obtained hafnium ingot is further subject to deoxidation with molten salt.
- 20 6. The manufacturing method of high purity hafnium according to claim 5 wherein, after performing deoxidation with molten salt, electron beam melting is further performed.